

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 02-203517
(43)Date of publication of application : 13.08.1990

(51)Int.CI. H01L 21/205

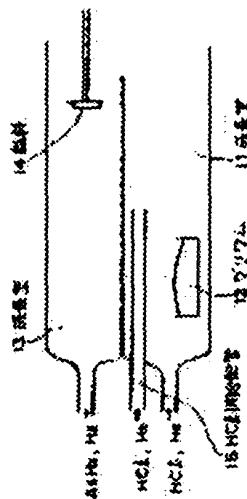
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(54) SELECTIVE VAPOR-PHASE EPITAXY OF III-V COMPOUND SEMICONDUCTOR

(57)Abstract:

PURPOSE: To realize a monomolecular vapor growth on a substrate having openings with different widths by performing alternately a process of supplying a group III element material and hydrogen chloride simultaneously and a process of supplying a group V element material.

CONSTITUTION: A substrate sample 14 having a mask of SiO₂ partially opened is put within a growing chamber 13 and is heated to a predetermined temperature. Then, HCl is supplied over Ga 12 in a growing chamber 11 and GaCl thus produced is supplied together with HCl from a supply tube 18 so that a mixed atmosphere is established within the growing region. The sample 14 is transferred to the growing chamber 11 and exposed to the mixed atmosphere for a predetermined period of time. Then, the sample 14 is returned to the chamber 13 and AsH₃ is supplied to form a GaAs layer in the openings. Thereafter, the chamber 13 is purged of AsH₃. These procedures are repeated to grow the GaAs layer. In this manner, thickness per ALE cycle can be controlled by a unit of monomolecular layer in the selective growth on the substrate having openings with different widths.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]